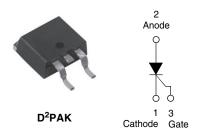


Vishay Semiconductors

# Surface Mountable Phase Control SCR, 16 A



| PRODUCT SUMMARY        |         |  |  |  |  |  |
|------------------------|---------|--|--|--|--|--|
| V <sub>T</sub> at 10 A | < 1.4 V |  |  |  |  |  |
| I <sub>TSM</sub>       | 200 A   |  |  |  |  |  |
| V <sub>RRM</sub>       | 1600 V  |  |  |  |  |  |

#### **FEATURES**

 Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C



• Compliant to RoHS directive 2002/95/EC

• Designed and qualified for industrial level

#### **APPLICATIONS**

- Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are in identical package outlines

### **DESCRIPTION**

The VS-16TTS16SPbF High Voltage Series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

| OUTPUT CURRENT IN TYPICAL APPLICATIONS                                |      |      |   |  |  |  |  |  |  |
|---|------|------|---|--|--|--|--|--|--|
| APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS             |      |      |   |  |  |  |  |  |  |
| NEMA FR-4 or G-10 glass fabric-based epoxy with 4 oz. (140 μm) copper | 2.5  | 3.5  |   |  |  |  |  |  |  |
| Aluminum IMS, R <sub>thCA</sub> = 15 °C/W                             | 6.3  | 9.5  | A |  |  |  |  |  |  |
| Aluminum IMS with heatsink, R <sub>thCA</sub> = 5 °C/W                | 14.0 | 18.5 |   |  |  |  |  |  |  |

#### Note

•  $T_A = 55$  °C,  $T_J = 125$  °C, footprint 300 mm<sup>2</sup>

| MAJOR RATINGS AND CHARACTERISTICS  |                              |             |       |  |  |  |  |  |
|------------------------------------|------------------------------|-------------|-------|--|--|--|--|--|
| SYMBOL                             | CHARACTERISTICS              | VALUES      | UNITS |  |  |  |  |  |
| I <sub>T(AV)</sub>                 | Sinusoidal waveform          | 10          | ۸     |  |  |  |  |  |
| I <sub>RMS</sub>                   |                              | 16          | A     |  |  |  |  |  |
| V <sub>RRM</sub> /V <sub>DRM</sub> |                              | 1600        | V     |  |  |  |  |  |
| I <sub>TSM</sub>                   |                              | 200         | A     |  |  |  |  |  |
| V <sub>T</sub>                     | 10 A, T <sub>J</sub> = 25 °C | 1.4         | V     |  |  |  |  |  |
| dV/dt                              |                              | 500         | V/µs  |  |  |  |  |  |
| dl/dt                              |                              | 150         | A/µs  |  |  |  |  |  |
| T <sub>J</sub>                     |                              | - 40 to 125 | °C    |  |  |  |  |  |

| VOLTAGE RATINGS |   |  |   |  |  |  |  |  |  |
|-----------------|---|--|---|--|--|--|--|--|--|
| PART NUMBER     | V <sub>RRM</sub> , MAXIMUM PEAK<br>REVERSE VOLTAGE<br>V | V <sub>DRM</sub> , MAXIMUM PEAK<br>DIRECT VOLTAGE<br>V | I <sub>RRM</sub> /I <sub>DRM</sub><br>AT 125 °C<br>mA |  |  |  |  |  |  |
| VS-16TTS16SPbF  | 1600  | 1600   | 10  |  |  |  |  |  |  |

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### Surface Mountable Phase Control SCR, 16 A



Document Number: 94590

Revision: 16-Jul-10

| ABSOLUTE MAXIMUM RATINGS                   |                                  |  |      |        |                    |  |  |
|--|----------------------------------|--|------|--------|--------------------|--|--|
| PARAMETER                                  | SYMBOL                           | TEST CONDITIONS  | VAL  | VALUES |                    |  |  |
| PANAIVIETEN                                | STINIBUL                         | TEST CONDITIONS  | TYP. | MAX.   | UNITS              |  |  |
| Maximum average on-state current           | I <sub>T(AV)</sub>               | T <sub>C</sub> = 93 °C, 180° conduction, half sine wave          | 1    | 10     |                    |  |  |
| Maximum RMS on-state current               | I <sub>RMS</sub>                 |  | 1    | 6      | Α                  |  |  |
| Maximum peak, one-cycle,                   | <b>I</b>                         | 10 ms sine pulse, rated V <sub>RRM</sub> applied                 | 1    | 70     |                    |  |  |
| non-repetitive surge current               | I <sub>TSM</sub>                 | 10 ms sine pulse, no voltage reapplied                           | 2    | 00     |                    |  |  |
| Maximum I <sup>2</sup> t for fusing        | l <sup>2</sup> t                 | 10 ms sine pulse, rated V <sub>RRM</sub> applied                 | 144  |        | - A <sup>2</sup> s |  |  |
| Maximum 1-t for fusing                     | 1-1                              | 10 ms sine pulse, no voltage reapplied                           | 200  |        |                    |  |  |
| Maximum I <sup>2</sup> √t for fusing       | I²√t                             | t = 0.1 ms to 10 ms, no voltage reapplied                        | 20   | 2000   |                    |  |  |
| Maximum on-state voltage drop              | $V_{TM}$                         | 10 A, T <sub>J</sub> = 25 °C                                     | 1.4  |        | V                  |  |  |
| On-state slope resistance                  | r <sub>t</sub>                   | T 105 %  |      | 24.0   |                    |  |  |
| Threshold voltage                          | V <sub>T(TO)</sub>               | T <sub>J</sub> = 125 °C  | 1.1  |        | V                  |  |  |
| Maximum reverse and direct leakage current | I <sub>RM</sub> /I <sub>DM</sub> | $T_J = 25 ^{\circ}\text{C}$                                      | 0.5  |        |                    |  |  |
| waximum reverse and direct leakage current |                                  | $V_R = Rated V_{RRM}/V_{DRM}$                                    | 1    | 10     |                    |  |  |
| Holding current                            | I <sub>H</sub>                   | Anode supply = 6 V, resistive load, initial I <sub>T</sub> = 1 A |      | 150    | mA                 |  |  |
| Maximum latching current                   | ΙL                               | Anode supply = 6 V, resistive load                               | 200  |        |                    |  |  |
| Maximum rate of rise of off-state voltage  | dV/dt                            |  | 500  |        | V/µs               |  |  |
| Maximum rate of rise of turned-on current  | dl/dt                            |  | 150  |        | A/µs               |  |  |

| TRIGGERING                                  |                    |  |        |       |  |  |  |  |
|---|--------------------|--|--------|-------|--|--|--|--|
| PARAMETER                                   | SYMBOL             | TEST CONDITIONS  | VALUES | UNITS |  |  |  |  |
| Maximum peak gate power                     | P <sub>GM</sub>    |  | 8.0    | W     |  |  |  |  |
| Maximum average gate power                  | P <sub>G(AV)</sub> |  | 2.0    | VV    |  |  |  |  |
| Maximum peak positive gate current          | + I <sub>GM</sub>  |  | 1.5    | Α     |  |  |  |  |
| Maximum peak negative gate voltage          | - V <sub>GM</sub>  |  | 10     | V     |  |  |  |  |
|   | I <sub>GT</sub>    | Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C | 90     | mA    |  |  |  |  |
| Maximum required DC gate current to trigger |                    | Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C   | 60     |       |  |  |  |  |
|   |                    | Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C  | 35     |       |  |  |  |  |
|   |                    | Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C | 3.0    |       |  |  |  |  |
| Maximum required DC gate voltage to trigger | $V_{\mathrm{GT}}$  | Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C   | 2.0    | v     |  |  |  |  |
| voltage to trigger                          |                    | Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C  | 1.0    | V     |  |  |  |  |
| Maximum DC gate voltage not to trigger      | $V_{GD}$           | T 105 °C V Detect value                                      | 0.25   |       |  |  |  |  |
| Maximum DC gate current not to trigger      | $I_{GD}$           | T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = Rated value      | 2.0    | mA    |  |  |  |  |

| SWITCHING                     |                 |                         |        |       |  |  |  |
|-------------------------------|-----------------|-------------------------|--------|-------|--|--|--|
| PARAMETER                     | SYMBOL          | TEST CONDITIONS         | VALUES | UNITS |  |  |  |
| Typical turn-on time          | t <sub>gt</sub> | T <sub>J</sub> = 25 °C  | 0.9    |       |  |  |  |
| Typical reverse recovery time | t <sub>rr</sub> | T. – 195 °C             | 4      | μs    |  |  |  |
| Typical turn-off time         | t <sub>q</sub>  | T <sub>J</sub> = 125 °C | 110    |       |  |  |  |

### Surface Mountable Phase Control SCR, 16 A

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| THERMAL - MECHANICAL SPECIFICATIONS             |                                   |  |             |       |  |  |  |  |
|---|-----------------------------------|--|-------------|-------|--|--|--|--|
| PARAMETER                                       | SYMBOL                            | VALUES                                     | UNITS       |       |  |  |  |  |
| Maximum junction and storage temperature range  | T <sub>J</sub> , T <sub>Stg</sub> |  | - 40 to 125 | °C    |  |  |  |  |
| Soldering temperature                           | T <sub>S</sub>                    | T <sub>S</sub> For 10 s (1.6 mm from case) |             |       |  |  |  |  |
| Maximum thermal resistance, junction to case    | R <sub>thJC</sub>                 | DC operation                               | 1.3         | 20.44 |  |  |  |  |
| Typical thermal resistance, junction to ambient | R <sub>thJA</sub>                 | PCB mount (1)                              | 40          | °C/W  |  |  |  |  |
| Approximate weight                              |                                   |  | 2           | g     |  |  |  |  |
| Approximate weight                              |                                   |  | 0.07        | OZ.   |  |  |  |  |
| Marking device                                  |                                   | Case style D <sup>2</sup> PAK (SMD-220)    | 16TTS       | 16S   |  |  |  |  |

#### Note

<sup>(1)</sup> When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 μm) copper 40 °C/W. For recommended footprint and soldering techniques refer to application note #AN-994.

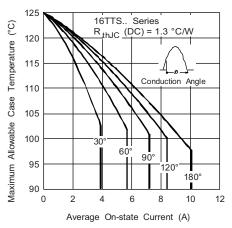


Fig. 1 - Current Rating Characteristics

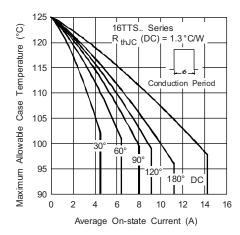


Fig. 2 - Current Rating Characteristics

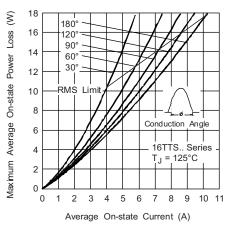


Fig. 3 - On-State Power Loss Characteristics

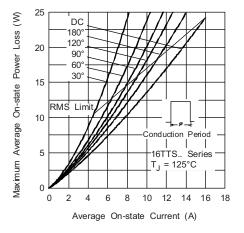


Fig. 4 - On-State Power Loss Characteristics

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### Surface Mountable Phase Control SCR, 16 A



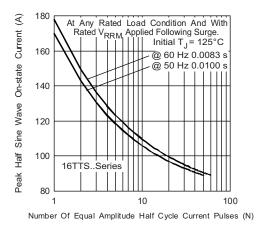


Fig. 5 - Maximum Non-Repetitive Surge Current

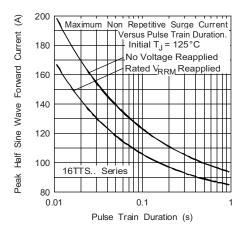


Fig. 6 - Maximum Non-Repetitive Surge Current

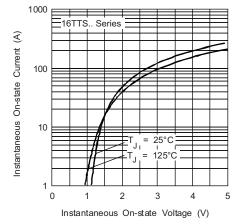


Fig. 7 - On-State Voltage Drop Characteristics

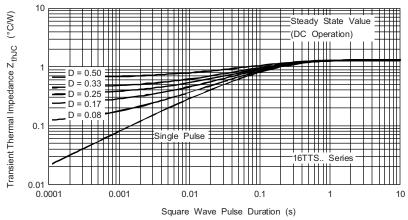


Fig. 8 - Thermal Impedance Z<sub>thJC</sub> Characteristics

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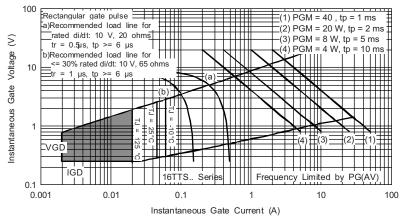
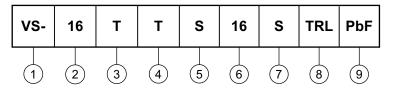


Fig. 9 - Gate Characteristics

### **ORDERING INFORMATION TABLE**

Device code



- 1 HPP product suffix
- 2 Current rating
- 3 Circuit configuration:
  - T = Single thyristor
- 4 Package:
  - T = TO-220AC
- 5 Type of silicon:
  - S = Standard recovery rectifier
- 6 Voltage rating: Voltage code x 100 = V<sub>RRM</sub> (16 = 1600 V)
- **7** S = TO-220 D<sup>2</sup>PAK (SMD-220) version
- | 8 | • None = Tube
  - TRL = Tape and reel (left oriented)
  - TRR = Tape and reel (right oriented)
- 9 PbF = Lead (Pb)-free

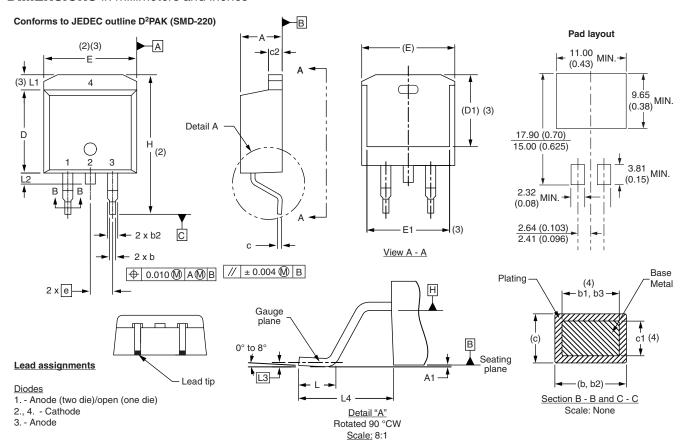
| LINKS TO RELATED DOCUMENTS |                          |  |  |  |  |  |
|----------------------------|--------------------------|--|--|--|--|--|
| Dimensions                 | www.vishay.com/doc?95046 |  |  |  |  |  |
| Part marking information   | www.vishay.com/doc?95054 |  |  |  |  |  |
| Packaging information      | www.vishay.com/doc?95032 |  |  |  |  |  |



### Vishay Semiconductors

### D<sup>2</sup>PAK

#### **DIMENSIONS** in millimeters and inches



| SYMBOL | MILLIN | MILLIMETERS |       | HES   | HES NOTES |  | SYMBOL   | MILLIM | ETERS | INC   | HES   |
|--------|--------|-------------|-------|-------|-----------|--|----------|--------|-------|-------|-------|
| STWBOL | MIN.   | MAX.        | MIN.  | MAX.  | NOTES     |  | STINIBUL | MIN.   | MAX.  | MIN.  | MAX.  |
| Α      | 4.06   | 4.83        | 0.160 | 0.190 |           |  | D1       | 6.86   | 8.00  | 0.270 | 0.315 |
| A1     | 0.00   | 0.254       | 0.000 | 0.010 |           |  | E        | 9.65   | 10.67 | 0.380 | 0.420 |
| b      | 0.51   | 0.99        | 0.020 | 0.039 |           |  | E1       | 7.90   | 8.80  | 0.311 | 0.346 |
| b1     | 0.51   | 0.89        | 0.020 | 0.035 | 4         |  | е        | 2.54   | BSC   | 0.100 | BSC   |
| b2     | 1.14   | 1.78        | 0.045 | 0.070 |           |  | Н        | 14.61  | 15.88 | 0.575 | 0.625 |
| b3     | 1.14   | 1.73        | 0.045 | 0.068 | 4         |  | L        | 1.78   | 2.79  | 0.070 | 0.110 |
| С      | 0.38   | 0.74        | 0.015 | 0.029 |           |  | L1       | -      | 1.65  | -     | 0.066 |
| c1     | 0.38   | 0.58        | 0.015 | 0.023 | 4         |  | L2       | 1.27   | 1.78  | 0.050 | 0.070 |
| c2     | 1.14   | 1.65        | 0.045 | 0.065 |           |  | L3       | 0.25   | BSC   | 0.010 | BSC   |
| D      | 8.51   | 9.65        | 0.335 | 0.380 | 2         |  | L4       | 4.78   | 5.28  | 0.188 | 0.208 |

#### Notes

- $^{(1)}$  Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC outline TO-263AB

**NOTES** 

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2, 3

3

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